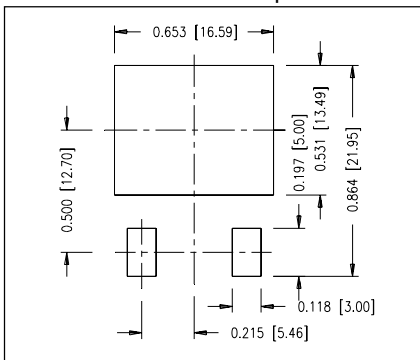


Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, Note 2	14	24	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3900	pF
C_{oss}			500	pF
C_{rss}			130	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External),		28	ns
t_r			30	ns
$t_{d(off)}$			55	ns
t_f			16	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		95	nC
Q_{gs}			27	nC
Q_{gd}			40	nC
R_{thJC}	(TO-247)			0.42 K/W
R_{thCK}			0.25	K/W

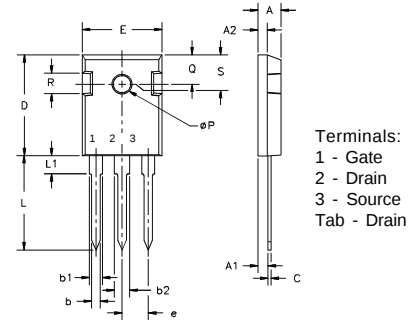
Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	24N50Q 26N50Q		24 A 26 A
I_{SM}	Repetitive; Note1	24N50Q 26N50Q		96 A 104 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.3 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		0.85	250 ns
Q_{RM}				μC
I_{RM}			8	A

Note 1. Pulse width limited by T_{JM}
2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

Min Recommended Footprint

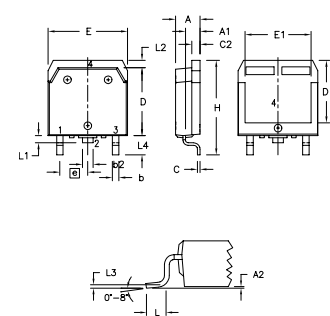


TO-247 AD Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

TO-268 Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.9 5.1	.193 .201
A ₁	2.7 2.9	.106 .114
A ₂	.02 .25	.001 .010
b	1.15 1.45	.045 .057
b ₁	1.9 2.1	.075 .083
b ₂	.4 .65	.016 .026
D	13.80 14.00	.543 .551
E	15.85 16.05	.624 .632
E ₁	13.3 13.6	.524 .535
e	5.45 BSC	.215 BSC
H	18.70 19.10	.736 .752
L	2.40 2.70	.094 .106
L1	1.20 1.40	.047 .055
L2	1.00 1.15	.039 .045
L3	0.25 BSC	.010 BSC
L4	3.80 4.10	.150 .161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

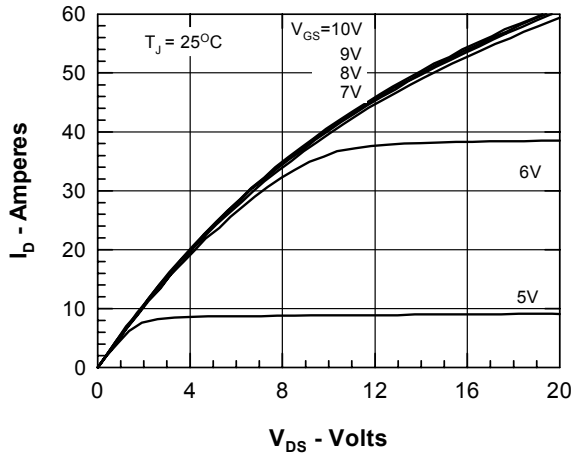


Fig.1 Output Characteristics @ $T_J = 25^\circ\text{C}$

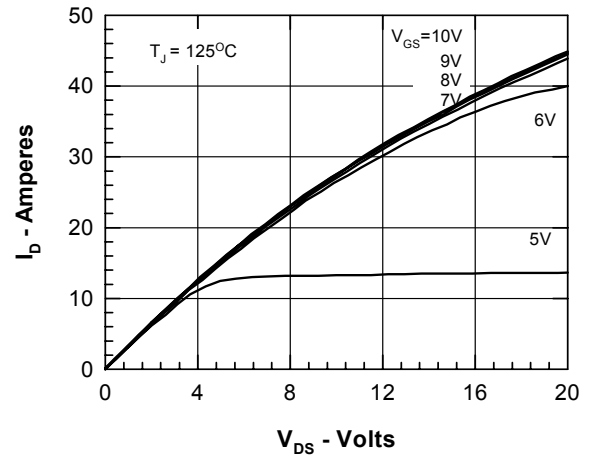


Fig.2 Output Characteristics @ $T_J = 125^\circ\text{C}$

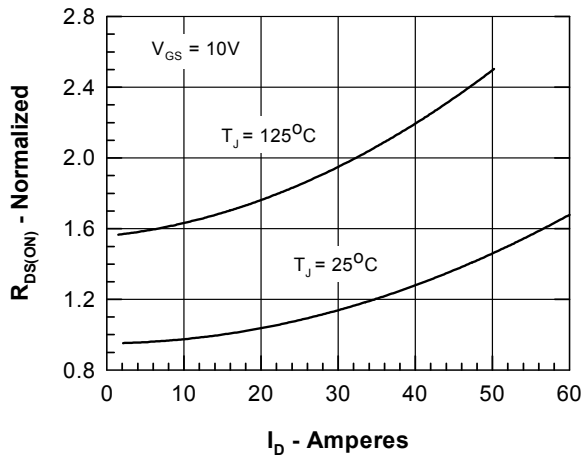


Fig.3 $R_{DS(on)}$ vs. Drain Current

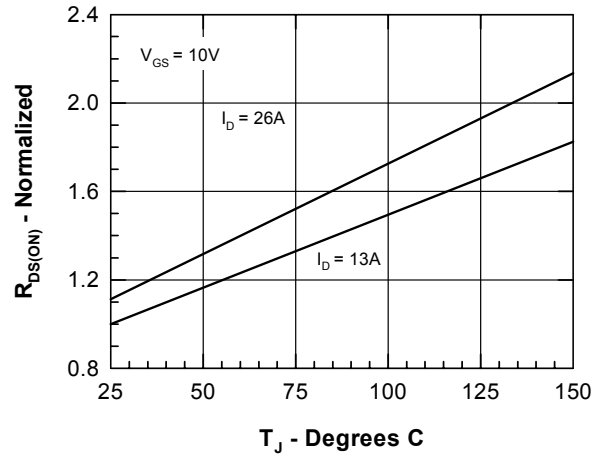


Fig.4 Temperature Dependence of Drain to Source Resistance

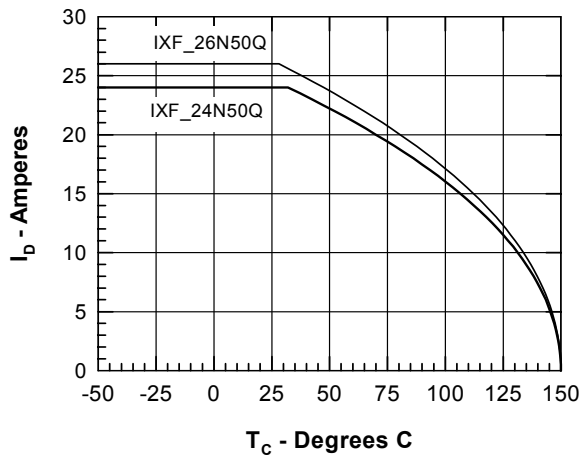


Fig.5 Drain Current vs. Case Temperature

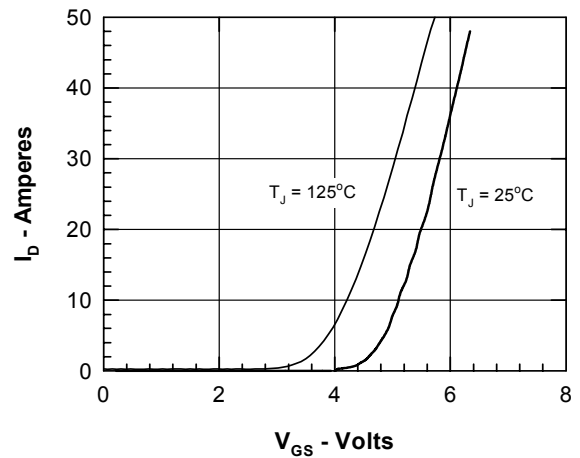


Fig.6 Drain Current vs Gate Source Voltage

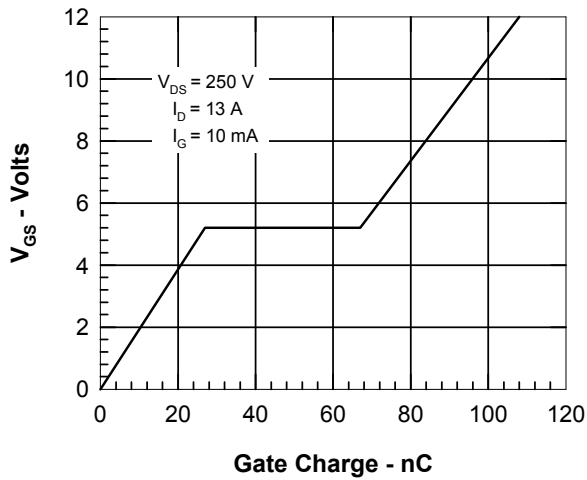


Fig.7 Gate Charge Characteristic Curve

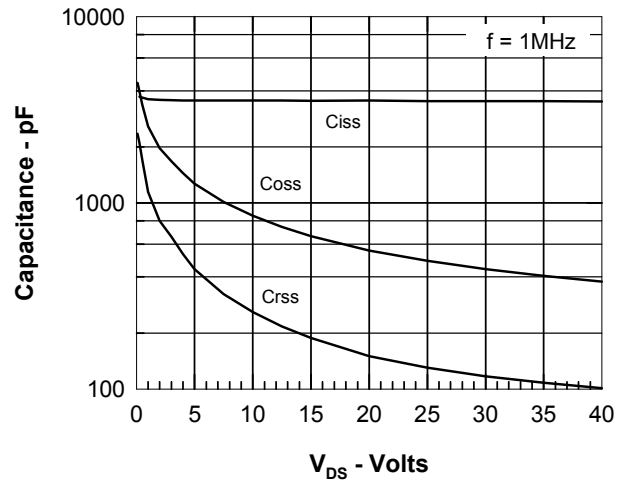


Fig.8 Capacitance Curves

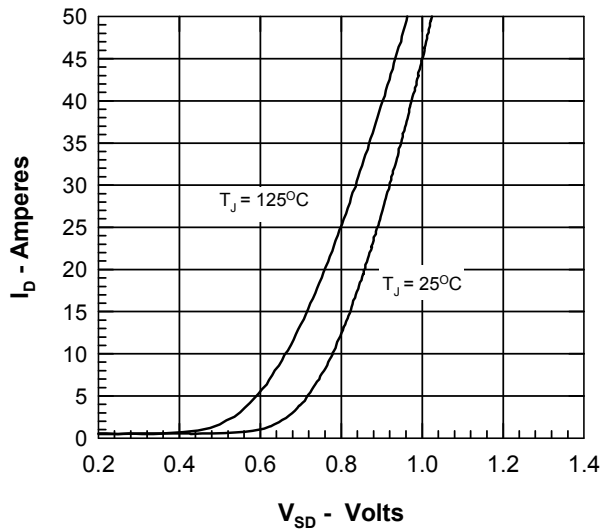


Fig.9 Drain Current vs Drain to Source Voltage

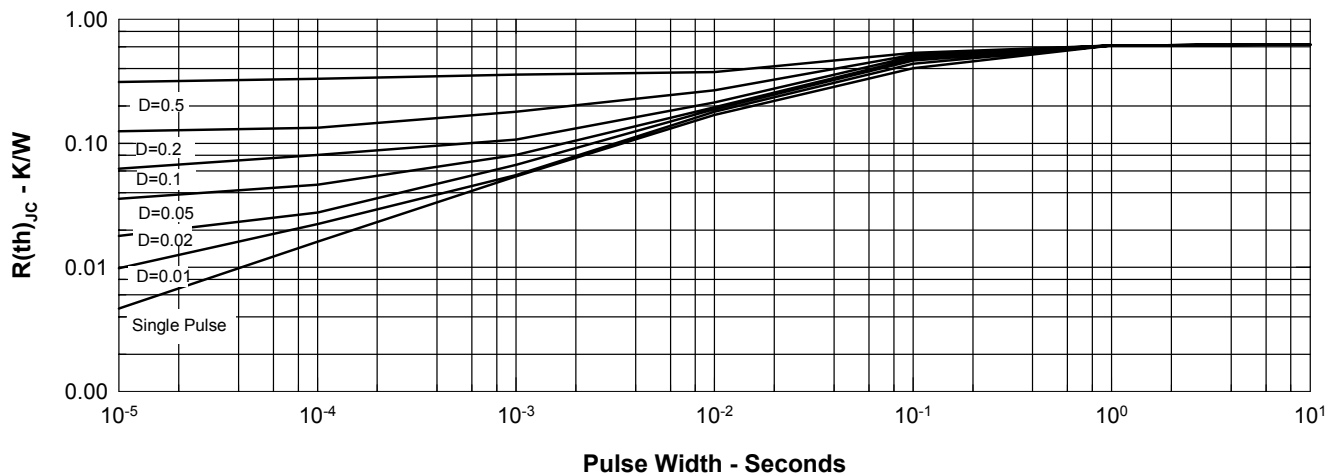


Fig.10 Transient Thermal Impedance

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.